

# SILICON POWER TRANSISTOR 2SA1647, 2SA1647-Z

# PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1647 is a mold power transistor developed for highspeed switching and features a very low collector-to-emitter saturation voltage.

This transistor is ideal for use in switching regulators, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for high-current switching.

#### **FEATURES**

- · Available for high-current control in small dimension
- · Z type is a lead processed product and is deal for mounting a hybrid IC.
- Low collector saturation voltage:  $V_{CE(sat)} = -0.3 \text{ V MAX.}$  (@Ic = -3 A)
- · Fast switching speed:  $t_f = 0.4 \ \mu s \ MAX. \ (@Ic = -3 \ A)$
- · High DC current gain and excellent linearity

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ )

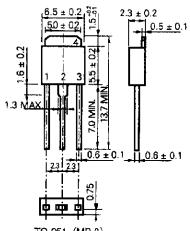
Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	-150	V
Collector to emitter voltage	VCEO	-100	V
Base to emitter voltage	VEBO	-7.0	V
Collector current (DC)	Ic(DC)	-5.0	Α
Collector current (pulse)	IC(pulse)*	-10	Α
Base current (DC)	I <sub>B(DC)</sub>	-2.5	Α
Total power dissipation	P⊤ (Tc = 25 °C)	18	W
Total power dissipation	PT (T <sub>A</sub> = 25 °C)	1.0**, 2.0***	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

\*: PW  $\leq$  10 ms, duty cycle  $\leq$  50%

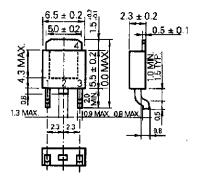
\*\*: Printing board mounted

\*\*\*:  $7.5 \text{ mm}^2 \times 0.7 \text{ mm}$  ceramic board mounted

#### PACKAGE DRAWING (UNIT: mm)



TO-251 (MP-3)



TO-252 (MP-3Z)

**Electrode Connection** 

- 1. Base
- 2. Collector
- 3. Emitter

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## ELECTINGA64 CHARACTERISTICS (TA = 25°C)

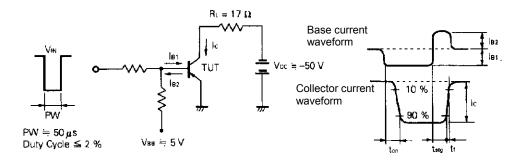
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	Ic = -2.5 A, I <sub>B</sub> = -0.25 A, L = 1 mH	-100			V
Collector to emitter voltage	VCEX(SUS)	$I_{C} = -2.5 \text{ A}, I_{B1} = -I_{B2} = -0.25 \text{ A},$ $V_{BE(OFF)} = 1.5 \text{ V}, L = 180 \ \mu\text{H}, clamped$				V
Collector cutoff current	Ісво	V <sub>CB</sub> = -100 V, I <sub>E</sub> = 0			-10	μΑ
Collector cutoff current	ICER	VCE = $-100$ V, RBE = $50~\Omega$ , TA = $125~^{\circ}$ C			-1.0	mA
Collector cutoff current	ICEX1	Vce = -100 V, Vbe(off) = 1.5 V			-10	μΑ
Collector cutoff current	ICEX2	Vce = -100 V, Vbe(OFF) = 1.5 V, Ta = 125 °C			-1.0	mA
Emitter cutoff current	ІЕВО	V <sub>EB(OFF)</sub> = -5.0 V, Ic = 0			-10	μΑ
DC current gain	hFE1*	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -0.5 \text{ A}$	100			
DC current gain	h <sub>FE2</sub> *	Vce = -2.0 V, Ic = -1.0 A	100		400	
DC current gain	h <sub>FE3</sub> *	Vce = -2.0 V, Ic = -3.0 A	60			
Collector saturation voltage	VCE(sat)1*	$Ic = -3.0 \text{ A}, I_B = -0.15 \text{ A}$			-0.3	V
Collector saturation voltage	VCE(sat)2*	Ic = -4.0  A, IB = -0.2  A			-0.5	V
Base saturation voltage	VBE(sat)1*	Ic = -3.0 A, Iв = -0.15 A			-1.2	V
Base saturation voltage	V <sub>BE(sat)2</sub> *	$I_C = -4.0 \text{ A}, I_B = -0.2 \text{ A}$			-1.5	V
Collector capacitance	Cob	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1.0 MHz		110		pF
Gain bandwidth product	f⊤	Vce = -10 V, Ic = 0.5 A		90		MHz
Turn-on time	ton	$Ic = -3.0 \text{ A}, R_L = 17 \Omega,$			0.3	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.15 \text{ A}, \text{ Vcc } \cong -50 \text{ V}$ Refer to the test circuit.			1.5	μs
Fall time	tf	Tiolor to the test offcuit.			0.4	μs

<sup>\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%/Pulsed

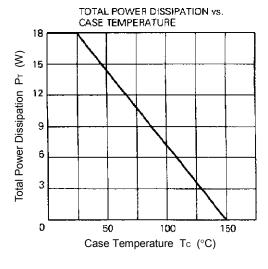
#### **hfe CLASSIFICATION**

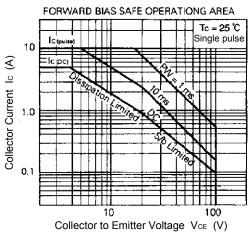
Marking	М	L	K
h <sub>FE2</sub>	100 to 200	150 to 300	200 to 400

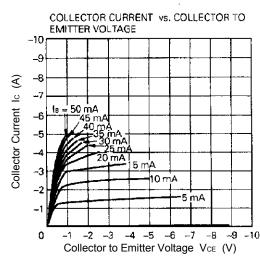
#### SWITCHING TIME TEST CIRCUIT

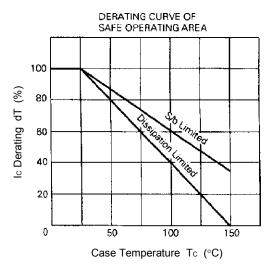


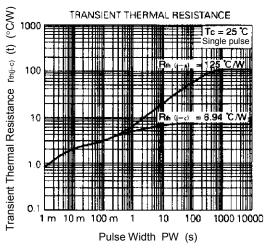
#### 查询"1281400A17"(共成用高CTERISTICS (TA = 25°C)

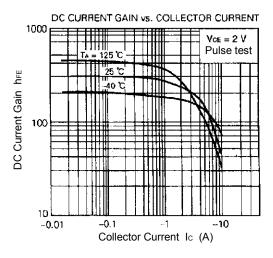




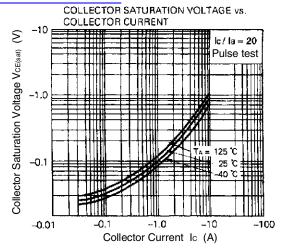


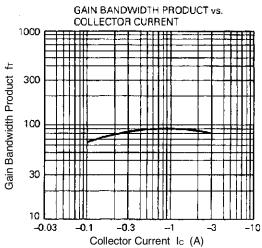


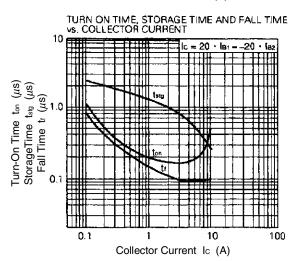


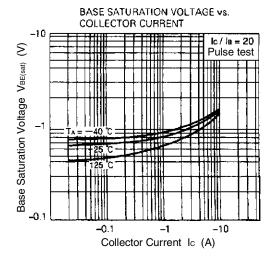


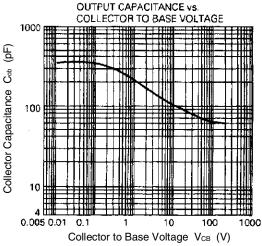
## 查询"2SA1647"供应商













查询[MEM6]7"供应商

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